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Response Under 37 C.F.R. § 1.116 - Expedited Procedure
Examining Group 2814

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony *et al.* Corres. and Mail
Appl. No.: 09/116,138 BOX AF
Filed: 07/15/98
For: High Permittivity Silicate Gate Dielectric

Docket: TI-24953
Examiner: A. Mai
Art Unit: 2814

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AMENDMENT PURSUANT TO 37 C.F.R. § 1.116

February 7, 2002

Ass't Commissioner for Patents
Washington, DC 20231

Examiner:

In response to the Office Action dated January 14, 2002, please amend the patent application as follows.

IN THE SPECIFICATION

A. Page 7, please add the following paragraphs at the bottom.
- Figs. 19-20 are cross-sectional views of a semiconductor device during fabrication according to a fifth preferred embodiment of the invention.
Fig. 21 is a simplified cross-sectional view of a field effect transistor using the current invention.--

B. Page 18, please add the following paragraph after line 2.
- Fig. 21 shows a simplified view of a completed transistor. Semiconductor substrate 100 has a channel region 120. Channel 120 is disposed between source 140 and drain 160. Conductive gate 38 overlies silicate gate dielectric 36.--